

# SPECIFICATION OF THICK FILM SOI WAFERS

Parameter	Unit	Specification
Silicon layer thickness	$\mu\text{m}$	4 – 100
Uniformity of silicon layer	$\mu\text{m}$	$\pm 1,0$
Surface roughness in the area of $2 \times 2 \mu\text{m}$	nm	$< 0,5$
Buried oxide thickness	$\mu\text{m}$	$< 2,0$
Uniformity of buried oxide layer	%	$< 5$
Total thickness variation (TTV)	$\mu\text{m}$	$< 5$
BOW	$\mu\text{m}$	$< 40$
WARP	$\mu\text{m}$	$< 40$
Type of conductivity		P, N
Orientation of silicon layer and substrate		$<100>$
Flat size	mm	$57,5 \pm 2,5$